



**ZX5T1951GQ** 

#### **60V PNP MEDIUM POWER TRANSISTOR IN SOT223**

## **Description**

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

### **Features**

- BV<sub>CEO</sub> > -60V
- I<sub>C</sub> = -6A Continuous Collector Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -95mV @ -1A</li>
- $R_{CE(sat)} = 40m\Omega$  for a low Equivalent On-Resistance
- h<sub>FE</sub> Specified up to -10A for a High Current Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZX5T1951GQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

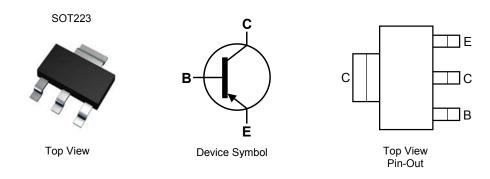
https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads;
   Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

## **Applications**

- Motor Driving
- DC-DC Modules
- Backlight Inverters
- Actuator, Relay and Solenoid Drivers



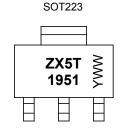
## Ordering Information (Note 4)

Ī	Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ı	ZX5T1951GQTA	ZX5T1951	7	12	1000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



ZX5T1951 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 0= 2020) WW or  $\overline{W}W$  = Week Code (01~53)



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-90	V
Collector-Emitter Voltage	V <sub>CES</sub>	-90	V
Collector-Emitter Voltage	$V_{CEO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current (Note 5)	lc	-6	Α
Peak Pulse Current	I <sub>CM</sub>	-15	Α
Base Current	lΒ	-1	A

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		3.0 24	W	
Linear Derating Factor	(Note 6)	- P <sub>D</sub>	1.6 12.8	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{ heta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	78	°C/W	
Thermal Resistance Junction to Lead (Note 7)		$R_{ heta JL}$	12.3		
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C		

# ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

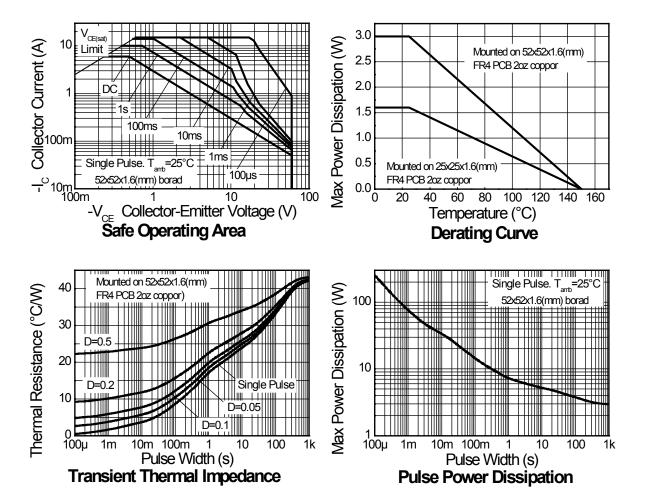
Notes:

- 5. For a device mounted with the collector lead on 52mm × 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 6, except the device is mounted on 25mm  $\times$  25mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics**





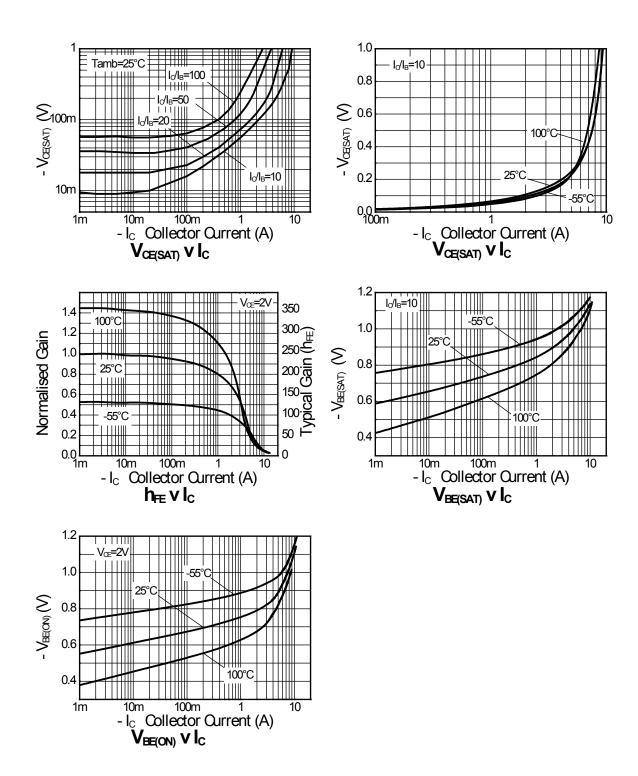
# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_CBO$	-90	-120	_	٧	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	-90	-120	_	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	$BV_CEO$	-60	-80		٧	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8		٧	$I_{E} = -100 \mu A$
Collector-Base Cut-Off Current	I <sub>CBO</sub>	_	-1	-50	nA	V <sub>CB</sub> = -72V
Collector-Emitter Cut-Off Current	I <sub>CES</sub>	_	-1	-50	nA	V <sub>CB</sub> = -72V
Emitter Cutoff Current	I <sub>EBO</sub>	_	-1	-10	nA	V <sub>EB</sub> = -6V
	h <sub>FE</sub>	100	240	_	_	$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
Static Forward Current Transfer Patic (Note 0)		100	180	300		I <sub>C</sub> = -2A, V <sub>CE</sub> = -2V
Static Forward Current Transfer Ratio (Note 9)		40	70	_		I <sub>C</sub> = -5A, V <sub>CE</sub> = -2V
		5	14	_		I <sub>C</sub> = -10A, V <sub>CE</sub> = -2V
	V <sub>CE(sat)</sub>	_	-16	-30	mV	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA
Callester Emitter Seturation Valtage (Note 0)		_	-55	-95		$I_C = -1A$ , $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 9)		_	-85	-130		$I_C = -2A$ , $I_B = -200mA$
		_	-200	-260		$I_C = -5A$ , $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	_	-1	-1.15	V	$I_C = -5A$ , $I_B = -500$ mV
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	_	-0.89	-1.0	٧	$I_C = -5A$ , $V_{CE} = -2V$
Output Capacitance (Note 9)	$C_{obo}$	_	33	70	pF	V <sub>CB</sub> = -10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	_	120	_	MHz	$V_{CE} = -10V, I_{C} = -100mA$ f = 50MHz
0.71.1.	t <sub>on</sub>	_	33	80		$V_{CC} = -10V, I_{C} = -2A$
Switching Time	t <sub>off</sub>	_	215	300	ns	$I_{B1} = -I_{B2} = -200$ mA

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

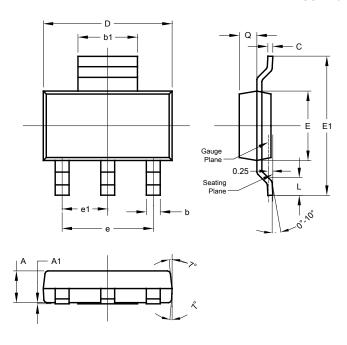




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT223**

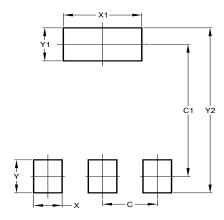


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
<b>E1</b> 6.90		7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT223**



Dimensions	Value (in mm)
С	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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